

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

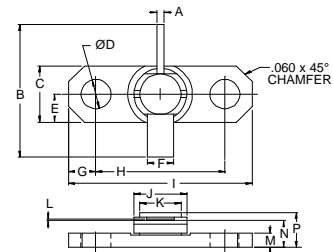
The **ASI MLN1030F** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	20 V
P_{DISS}	--- W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	20 °C/W

PACKAGE STYLE .250 2L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

ORDER CODE: ASI10622
CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1 mA	50			V
BV_{CEO}	I _C = 5 mA	20			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CEO}	V _{CE} = 18 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	15		120	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			5.0	pF
P_G	V _{CE} = 20 V P _{OUT} = 1.0 W f = 1.0 GHz I _{CQ} = 150 mA	12			dB